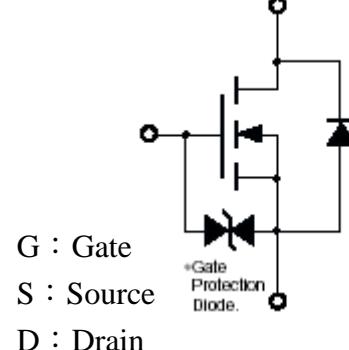
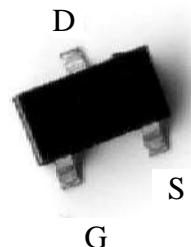


600V N-Channel Enhancement Mode MOSFET

Features:

- Lower gate charge
- ESD protected gate
- Pb-free lead plating and Halogen-free package

SOT-23



BV_{DSS}	600V
I _D @ V _{GS} =10V, T _A =25°C	33mA
R _{DSON(TYP)} @ V _{GS} =10V, I _D =16mA	165Ω
R _{DSON(TYP)} @ V _{GS} =4.5V, I _D =16mA	166Ω

G : Gate

S : Source

D : Drain

Ordering Information

Device	Package	Shipping
KWN127K	SOT-23 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$, unless otherwise noted)

Parameter		Symbol	Limits	Unit
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	$T_A=25^\circ\text{C}, V_{GS}=10\text{V}$	I_D	33	mA
	$T_A=70^\circ\text{C}, V_{GS}=10\text{V}$		26	
Pulsed Drain Current		I_{DM}	132 (Note 1 & 2)	
Power Dissipation	$T_A=25^\circ\text{C}$	P_D	0.5 (Note 3)	W
	$T_A=70^\circ\text{C}$		0.32 (Note 3)	
Gate Source ESD susceptibility		$V_{ESD(G-S)}$	3000 (Note 4)	V
Operating Junction and Storage Temperature		T_j, T_{stg}	-55 ~ +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction to Ambient , max	$R_{\theta JA}$	250 *3	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case, max	$R_{\theta JC}$	60	

Note : 1. Pulse width limited by maximum junction temperature.

2. Duty cycle $\leq 1\%$.

3. Surface mounted on min. copper pad.

4. Human body model, $1.5\text{k}\Omega$ in series with 100pF .

Electrical Characteristics ($T_A=25^\circ\text{C}$, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	600	-	-	V	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$
$V_{GS(\text{th})}$	1.5	-	3		$V_{DS}=V_{GS}, I_D=8\mu\text{A}$
I_{GSS}	-	-	± 10	μA	$V_{GS}=\pm 16\text{V}, V_{DS}=0\text{V}$
ID_{SS}	-	-	1		$V_{DS}=600\text{V}, V_{GS}=0\text{V}$
	-	-	10		$V_{DS}=600\text{V}, V_{GS}=0\text{V}, T_j=55^\circ\text{C}$
$*R_{DS(\text{ON})}^1$	-	165	250	Ω	$I_D=16\text{mA}, V_{GS}=10\text{V}$
	-	166	260		$I_D=16\text{mA}, V_{GS}=4.5\text{V}$
$*G_{FS}^1$	-	57	-	mS	$V_{DS}=40\text{V}, I_D=10\text{mA}$
Dynamic					
C_{iss}	-	21.4	32	pF	$V_{DS}=25\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$
C_{oss}	-	2.7	4		
C_{rss}	-	2.5	3.8		
$*t_{d(\text{ON})}^{1 \ 2}$	-	7.8	12	ns	$V_{DS}=300\text{V}, I_D=10\text{mA}, V_{GS}=10\text{V}, R_G=6\Omega$
$*t_r^{1 \ 2}$	-	22	33		
$*t_{d(\text{OFF})}^{1 \ 2}$	-	18.4	27.6		
$*t_f^{1 \ 2}$	-	92.8	139.2		

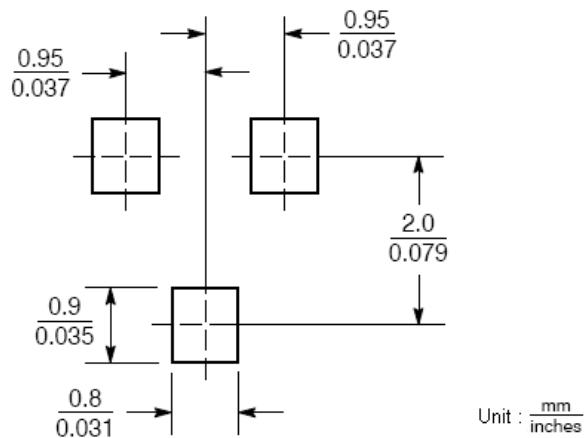
*Qg ^{1 2}	-	1.6	2.4	nC	V _{DS} =300V, I _D =10mA, V _{GS} =10V
*Qgs ^{1 2}	-	0.5	0.8		
*Qgd ^{1 2}	-	0.6	0.9		
Source-Drain Diode					
I _S	-	-	33	mA	
I _{SM} ³	-	-	132		
V _{SD} ¹	-	0.75	1		V _S =16mA, V _{GS} =0V
t _{rr} ¹	-	210	315		ns
Q _{rr} ¹	-	20	30		I _F =16mA, dI _F /dt=100A/μs

¹ Pulse test : Pulse width≤300μs, Duty cycle≤2%

² Independent of operating temperature

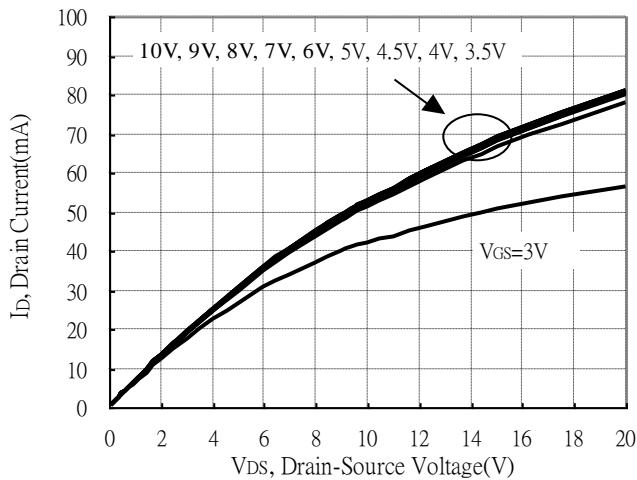
³ Pulse width limited by maximum junction temperature

Recommended Soldering Footprint

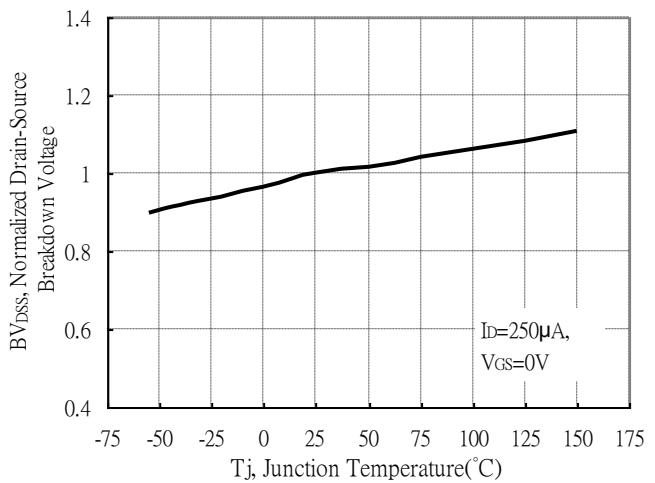


Typical Characteristics

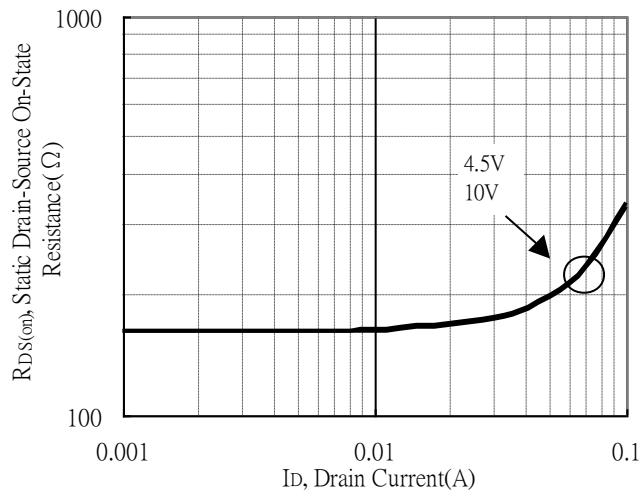
Typical Output Characteristics



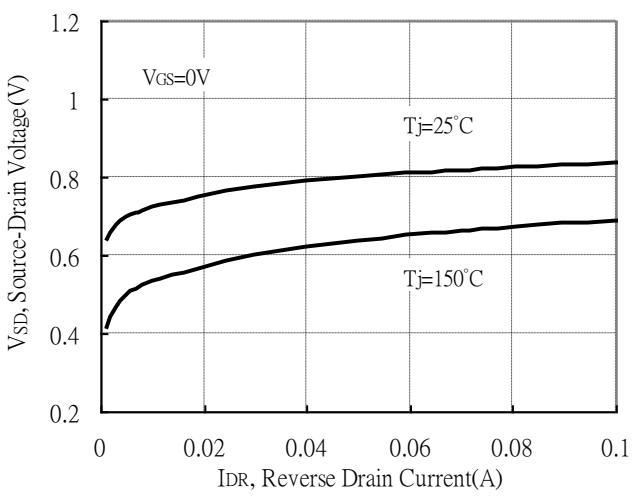
Brekdown Voltage vs Ambient Temperature



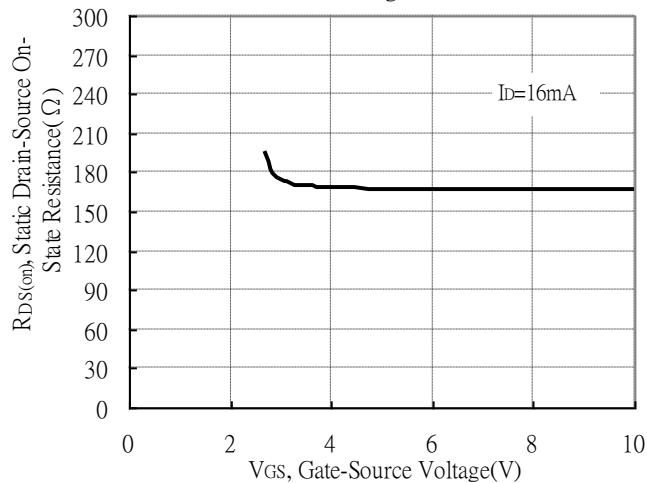
Static Drain-Source On-State resistance vs Drain Current



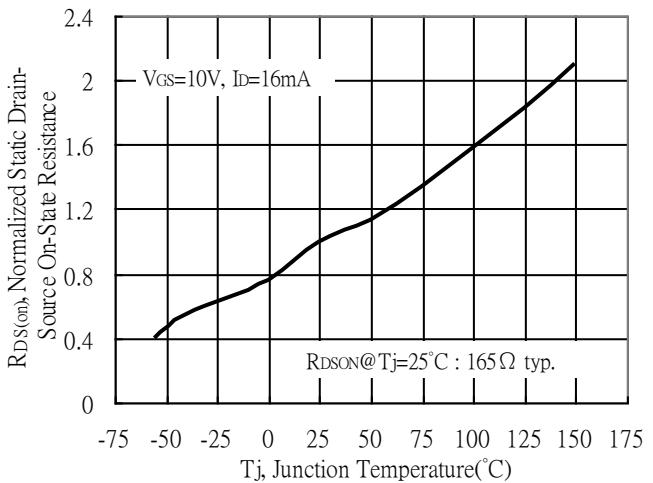
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

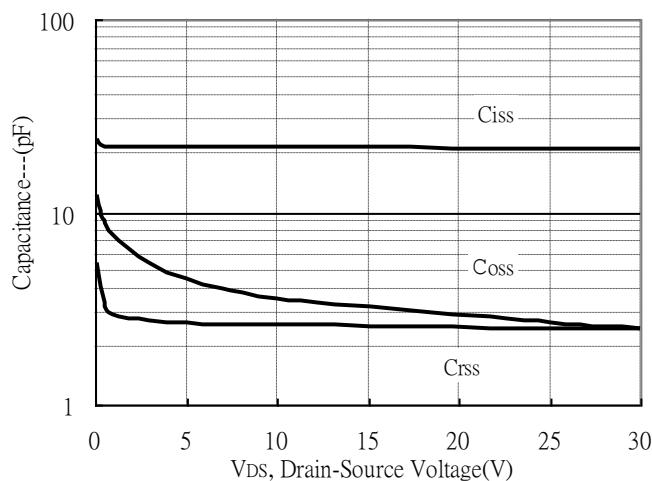


Drain-Source On-State Resistance vs Junction Temperature

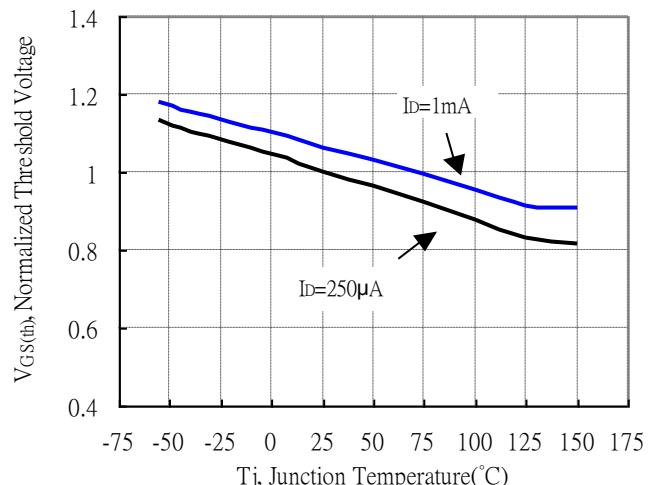


Typical Characteristics(Cont.)

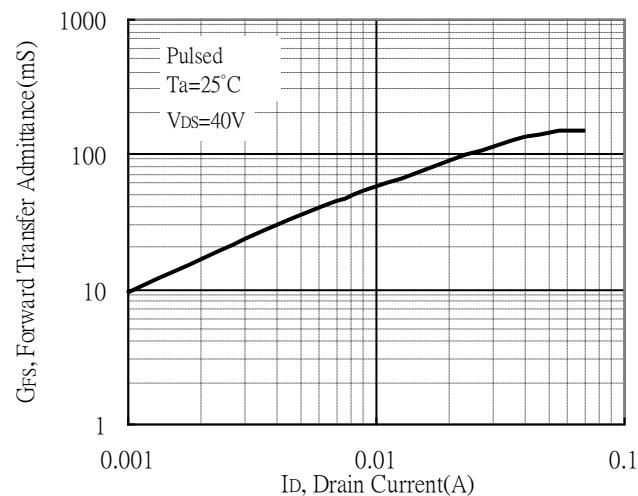
Capacitance vs Drain-to-Source Voltage



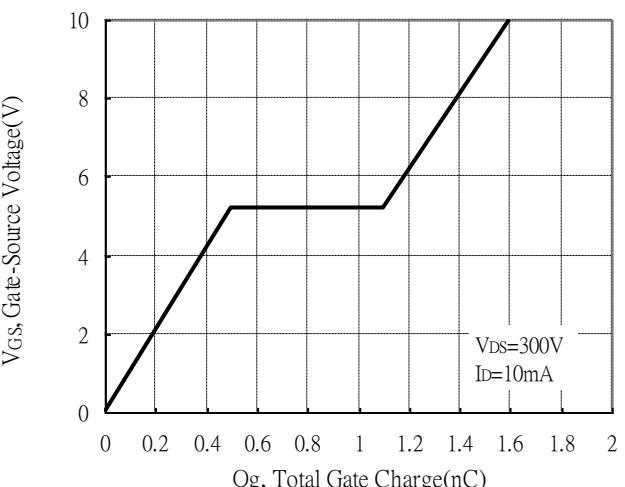
Threshold Voltage vs Junction Temperature



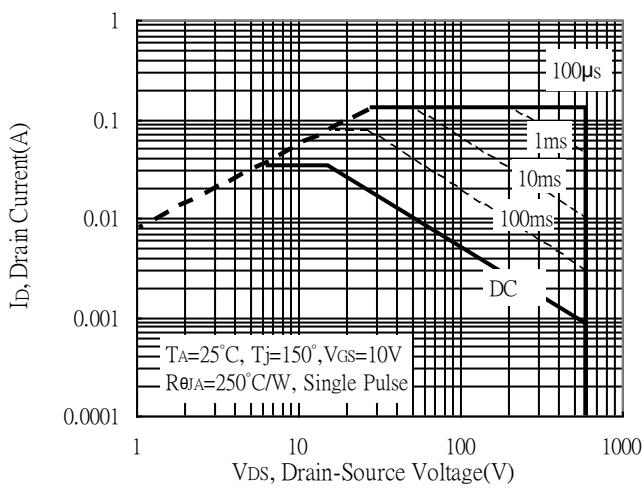
Forward Transfer Admittance vs Drain Current



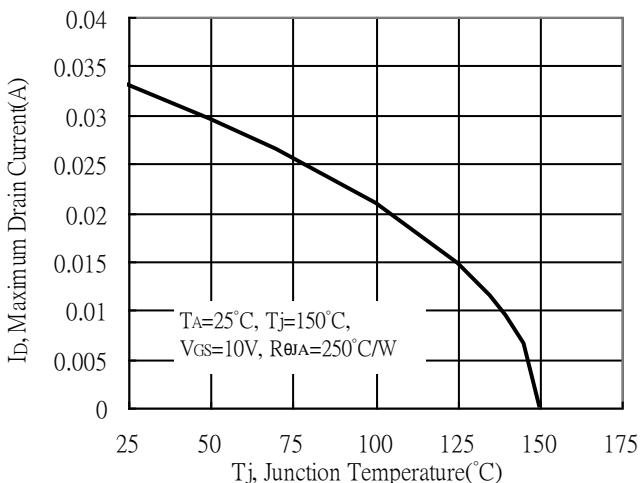
Gate Charge Characteristics



Maximum Safe Operating Area

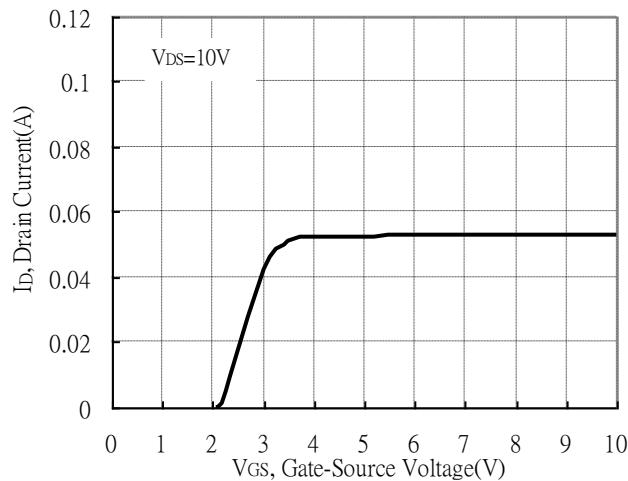


Maximum Drain Current vs Junction Temperature

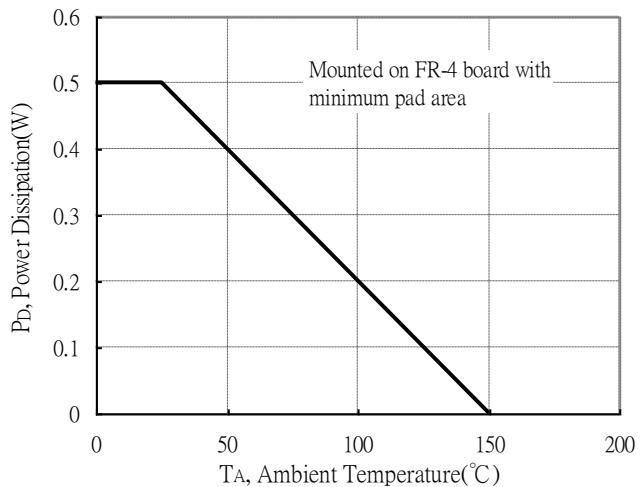


Typical Characteristics(Cont.)

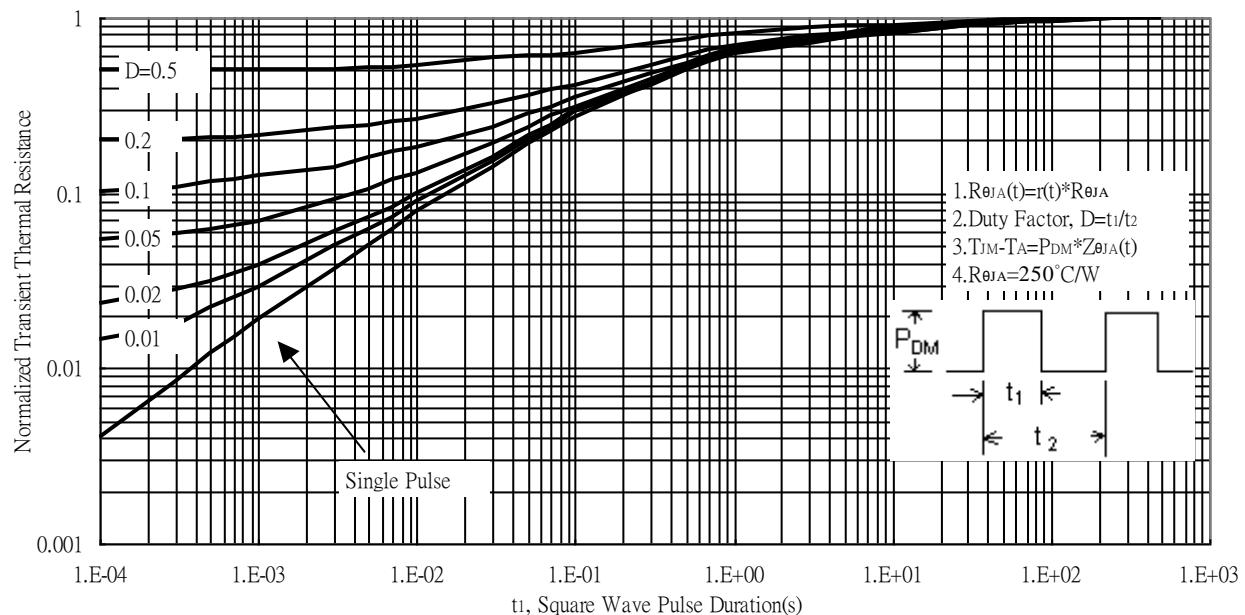
Typical Transfer Characteristics



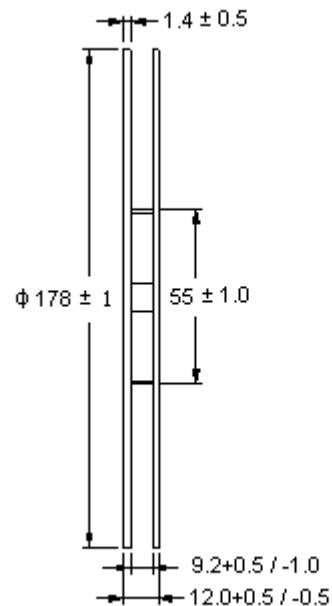
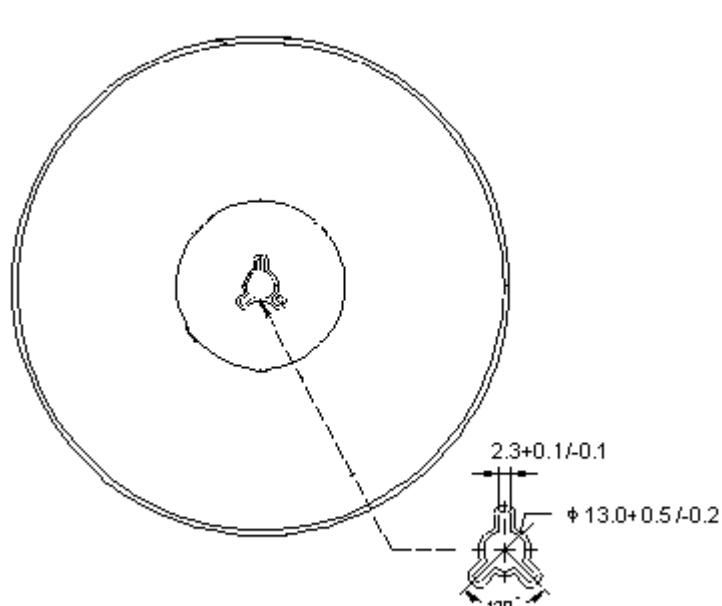
Power Derating Curve



Transient Thermal Response Curves

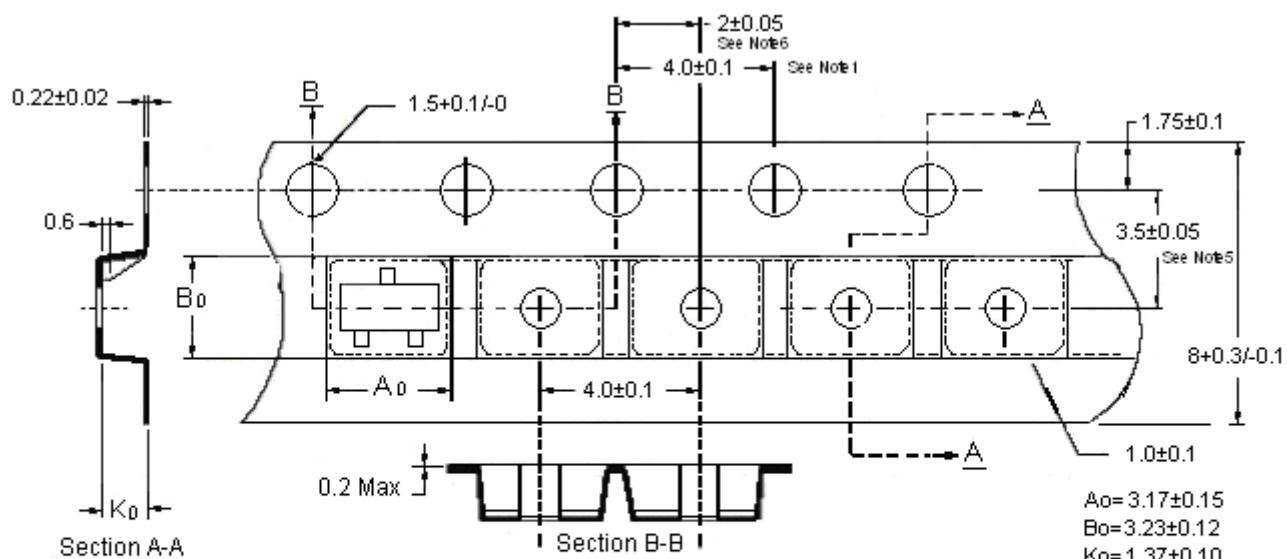


Reel Dimension



Unit: millimeter

Carrier Tape Dimension

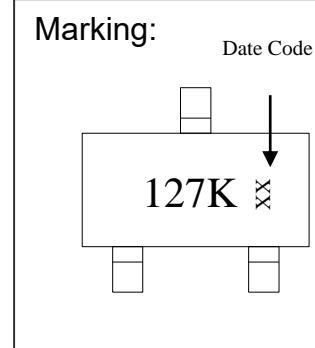
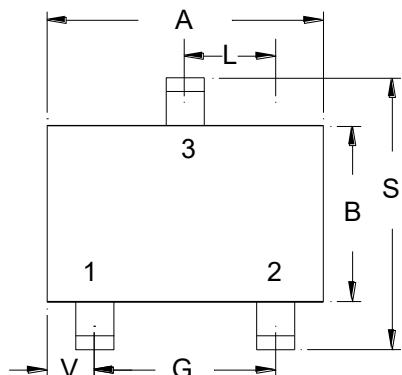


Notes:

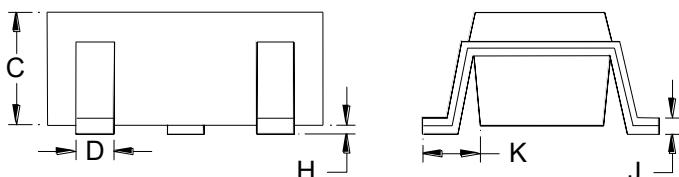
1. 10 sprocket hole pitch cumulative tolerance ± 0.2 .
2. Camber not to exceed 1mm in 100mm.
3. Material : conductive Black Polystyrene.
4. A_0 & B_0 measured on a plane 0.3mm above the bottom of the pocket.
5. K_0 measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

Unit : millimeter

SOT-23 Dimension



3-Lead SOT-23 Plastic Surface Mounted Package



Style: Pin 1.Gate 2.Source 3.Drain

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1063	0.1220	2.70	3.10	J	0.0034	0.0079	0.085	0.20
B	0.0472	0.0630	1.20	1.60	K	0.0128	0.0266	0.32	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1161	2.10	2.95
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0000	0.0040	0.00	0.10					